

1 **ABSTRACT OF THE DISCLOSURE**

2 The invention includes a semiconductive processing method of
3 electrochemical-mechanical removing at least some of a conductive
4 material from over a surface of a semiconductor substrate. A cathode
5 is provided at a first location of the wafer, and an anode is provided
6 at a second location of the wafer. The conductive material is polished
7 with the polishing pad polishing surface. The polishing occurs at a
8 region of the conductive material and not at another region. The region
9 where the polishing occurs is defined as a polishing operation location.
10 The polishing operation location is displaced across the surface of the
11 substrate from said second location of the substrate toward said first
12 location of the substrate. The polishing operation location is not
13 displaced from said first location toward said second location when the
14 polishing operation location is between the first and second locations.
15 The invention also includes a semiconductor processing method of
16 removing at least some of a conductive material from over a surface of
17 a semiconductive material wafer. A polishing pad is displaced across an
18 upper surface of the wafer from a central region of the wafer toward
19 a periphery of the wafer, and is not displaced from the periphery to the
20 central region.